

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Specimen)

NUS-03-001

Application Number

10/802,563

Applicant

Hong Yun Yu et al.

Filing Date

03/17/04

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SK	62251685	11/01	Gardner et al.	438	287	6/4/98
SK	6383879	5/7/02	Kizilyalli et al.	438	303	5/17/00
SK	6511911	1/28/03	Besser et al.	438	656	4/3/01
SK	6617624	9/9/03	Powell	257	288	3/15/01
SK	6043157	3/28/00	Gardner et al.	438	692	12/18/97
SK	5960270	9/28/99	Misra et al.	438	197	8/11/97
SK	6083836	7/4/00	Rodder	438	690	12/18/98
SK	6576967	6/10/03	Schaeffer, III et al.	257	411	9/18/00
SK	6479362	11/12/02	Cunningham	438	369	2/14/01
SK	6208004	3/27/01	Cunningham	257	413	8/19/98
SK	6051487	4/18/00	Gardner et al.	438	585	12/18/97

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SK	-	Heuss et al., Abstract C7.6 "Thermal Stability of Hafnium and Hafnium Nitride (HfN _x) Gate Electrodes on Silicon Dioxide," pp. 67, 76-77, Materials Res. Soc. Proc., April 2000.
SK	-	"Physical and Electrical Properties of Metal Gate Electrodes on HfO ₂ Gate Dielectrics," by J.K. Schaeffer et al., Journal of Vacuum Science and Tech., Vol. 21(1), Jan/Feb. 2003, pp. 11-17.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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[illegible][illegible]

SK	-	"Thermal Stability of PVD TiN Gate and Its Impacts on Characteristics of CMOS Transistors," by M. Wang et al., 6th Int'l Symp. on Plasma Process Induced Damage, May 4-15, 2001, Monterey, CA, USA, pp. 36-39.
SK	-	"Metal Gates for Advanced Sub-80-nm SOI CMOS Technology," by B. Cheng et al., 2001 IEEE Int'l SOI Conf., 10/01, pp. 91-92.

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

NUS-03-001

Application Number:

10/802,563

Applicant:

Hong Yu Yu et al.

Filing Date: 08/01/2014

03/17/04

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

SK	-	"Properties and Microelectronic Applications of Thin Films of Refractory Metal Nitrides", by M. Wittmar, Jnl. of Vacuum Science Tech. A, Vol. 3, pp. 1797-1803.
SK	-	"Int'l Tech. Roadmap for Semiconductor", Semiconductor Industry Association, San Jose, CA (ITRS-2003).

EXHIBIT A

DATE CONSIDERED

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SR	-	US Patent App. Pub. US 2003/0197230 A1 to Mocuta et al., Pub. Date 10/23/03, Filed 04/19/02, US Class 257/407.
SR	-	US Patent App. Pub. US 2002/0037615 A1 to Matsuo, Pub. Date 03/28/02, Filed 09/25/01, US Class 438/241.
SR		



5/20/05

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